

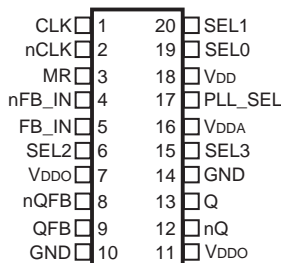
General Description

The 8745BI-21 is a highly versatile 1:1 LVDS Clock Generator. The 8745BI-21 has a fully integrated PLL and can be configured as a zero delay buffer, multiplier or divider, and has an output frequency range of 31.25MHz to 700MHz. The Reference Divider, Feedback Divider and Output Divider are each programmable, thereby allowing for the following output-to-input frequency ratios: 8:1, 4:1, 2:1, 1:1, 1:2, 1:4, 1:8. The external feedback allows the device to achieve “zero delay” between the input clock and the output clock. The PLL_SEL pin can be used to bypass the PLL for system test and debug purposes. In bypass mode, the reference clock is routed around the PLL and into the internal output dividers.

Features

- One differential LVDS output designed to meet or exceed the requirements of ANSI TIA/EIA-644 One differential feedback output pair
- Differential CLK, nCLK input pair
- CLKx, nCLKx pair can accept the following differential input levels: LVPECL, LVDS, LVHSTL, HCSSL, SSTL
- Output frequency range: 31.25MHz to 700MHz
- Input frequency range: 31.25MHz to 700MHz
- VCO range: 250MHz to 700MHz
- External feedback for “zero delay” clock regeneration with configurable frequencies
- Programmable dividers allow for the following output-to-input frequency ratios: 8:1, 4:1, 2:1, 1:1, 1:2, 1:4, 1:8
- Cycle-to-cycle jitter: 30ps (maximum)
- Output skew: 40ps (maximum)
- Static phase offset: 25ps ± 125ps
- Full 3.3V supply voltage
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package
- **For functional replacement part use 8T49N285**

Pin Assignments



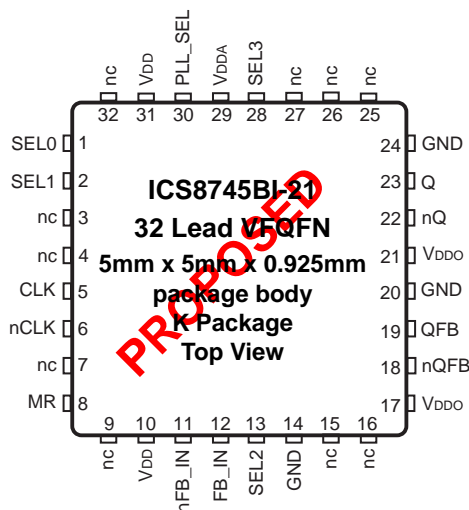
8745BI-21

20-Lead SOIC

7.5mm x 12.8mm x 2.3mm package body

M Package

Top View



Block Diagram

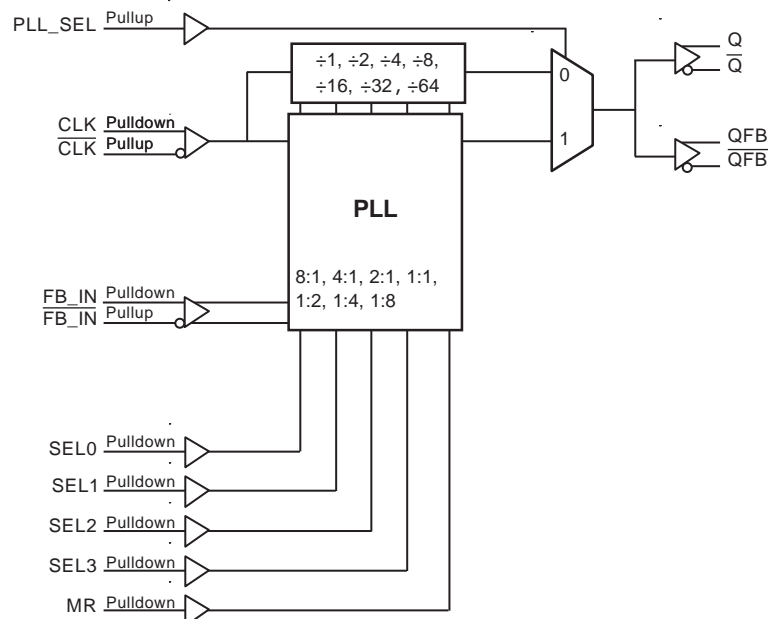


Table 1. Pin Descriptions

Number	Name	Type		Description
1	CLK	Input	Pulldown	Non-inverting differential clock input.
2	nCLK	Input	Pullup	Inverting differential clock input.
3	MR	Input	Pulldown	Active HIGH Master Reset. When logic HIGH, the internal dividers are reset causing the true output Q to go low and the inverted output nQ to go high. When logic LOW, the internal dividers and the outputs are enabled. LVCMOS / LVTTTL interface levels.
4	nFBIN	Input	Pullup	Inverting differential feedback input to phase detector for regenerating clocks with "Zero Delay."
5	FBIN	Input	Pulldown	Non-inverted differential feedback input to phase detector for regenerating clocks with "Zero Delay."
6, 15, 19, 20	SEL2, SEL3, SEL0 SEL1	Input	Pulldown	Determines output divider values in Table 3. LVCMOS / LVTTTL interface levels.
7, 11	V _{DDO}	Power		Output supply pins.
8, 9	nQFB/QFB	Output		Differential feedback output pair. LVDS interface levels.
10, 14	GND	Power		Power supply ground.
12, 13	nQ/Q	Output		Differential output pair. LVDS interface levels.
16	V _{DDA}	Power		Analog supply pin.
17	PLL_SEL	Input	Pullup	PLL select. Selects between the PLL and reference clock as the input to the dividers. When LOW, selects reference clock. LVCMOS/LVTTTL interface levels.
18	V _{DD}	Power		Core supply pin.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLUP}	Input Pullup Resistor			51		kΩ
R _{PULLDOWN}	Input Pulldown Resistor			51		kΩ

Function Tables

Table 3A. Control Input Function Table

Inputs					Outputs PLL_SEL = 1 PLL Enable Mode
SEL3	SEL2	SEL1	SEL0	Reference Frequency Range (MHz)*	Q, nQ
0	0	0	0	250 - 700	÷1
0	0	0	1	125 - 350	÷1
0	0	1	0	62.5 - 175	÷1
0	0	1	1	31.25 - 87.5	÷1
0	1	0	0	250 - 700	÷2
0	1	0	1	125 - 350	÷2
0	1	1	0	62.5 - 175	÷2
0	1	1	1	250 - 700	÷4
1	0	0	0	125 - 350	÷4
1	0	0	1	250 - 700	÷8
1	0	1	0	125 - 350	x2
1	0	1	1	62.5 - 175	x2
1	1	0	0	31.25 - 87.5	x2
1	1	0	1	62.5 - 175	x4
1	1	1	0	31.25 - 87.5	x4
1	1	1	1	31.25 - 87.5	x8

*NOTE: VCO frequency range for all configurations above is 250MHz to 700MHz.

Table 3B. PLL Bypass Function Table

Inputs				Outputs PLL_SEL = 0 PLL Bypass Mode
SEL3	SEL2	SEL1	SEL0	Q, nQ
0	0	0	0	÷4
0	0	0	1	÷4
0	0	1	0	÷4
0	0	1	1	÷8
0	1	0	0	÷8
0	1	0	1	÷8
0	1	1	0	÷16
0	1	1	1	÷16
1	0	0	0	÷32
1	0	0	1	÷64
1	0	1	0	÷2
1	0	1	1	÷2
1	1	0	0	÷4
1	1	0	1	÷1
1	1	1	0	÷2
1	1	1	1	÷1

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, I_O Continuous Current Surge Current	10mA 15mA
Package Thermal Impedance, θ_{JA} 20 Lead SOIC package 32 Lead VFQFN package	46.2°C/W (0 lfpm) 37°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

PROPOSED

DC Electrical Characteristics

Table 4A. LVDS Power Supply DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V_{DDA}	Analog Supply Voltage		3.135	3.3	3.465	V
V_{DDO}	Output Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current				128	mA
I_{DDA}	Analog Supply Current				18	mA
I_{DDO}	Output Supply Current				62	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage		2		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage		-0.3		0.8	V
I_{IH}	Input High Current	SEL[0:3], MR	$V_{DD} = V_{IN} = 3.465V$		150	μA
		PLL_SEL	$V_{DD} = V_{IN} = 3.465V$		5	μA
I_{IL}	Input Low Current	SEL[0:3], MR	$V_{DD} = 3.465V, V_{IN} = 0V$	-5		μA
		PLL_SEL	$V_{DD} = 3.465V, V_{IN} = 0V$	-150		μA

Table 4C. Differential DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
I_{IH}	Input High Current	CLK, FB_IN	$V_{DD} = V_{IN} = 3.465V$			150	μA
		nCLK, nFB_IN	$V_{DD} = V_{IN} = 3.465V$			5	μA
I_{IL}	Input Low Current	CLK, FB_IN	$V_{DD} = 3.465V,$ $V_{IN} = 0V$	-5			μA
		nCLK, nFB_IN	$V_{DD} = 3.465V,$ $V_{IN} = 0V$	-150			μA
V_{PP}	Peak-to-Peak Voltage; NOTE 1			0.15		1.3	V
V_{CMR}	Common Mode Input Voltage; NOTE 1, 2			GND + 0.5		$V_{DD} - 0.85$	V

NOTE 1: V_{IL} should not be less than -0.3V.

NOTE 2: Common mode input voltage is defined as V_{IH} .

Table 4D. LVDS DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OD}	Differential Output Voltage		320	440	550	mV
ΔV_{OD}	V_{OD} Magnitude Change			0	50	mV
V_{OS}	Offset Voltage		1.05	1.2	1.35	V
ΔV_{OS}	V_{OS} Magnitude Change				25	mV

Table 5. Input Frequency Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
F_{IN}	Input Frequency	CLK, nCLK	PLL_SEL = 1	31.25		700	μA
			PLL_SEL = 0			700	V

AC Electrical Characteristics

Table 6. AC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				700	MHz
t_{PD}	Propagation Delay; NOTE 1	PLL_SEL = 0V, $f \leq 700MHz$	2.9	3.4	4.0	ns
$t_{sk}(\emptyset)$	Static Phase Offset; NOTE 2, 5	PLL_SEL = 3.3V	-100	25	150	ps
$t_{sk}(o)$	Output Skew; NOTE 3, 5				40	ps
$f_{jit}(cc)$	Cycle-to-Cycle Jitter; NOTE 5, 6				30	ps
$f_{jit}(\theta)$	Phase Jitter; NOTE 4, 5, 6				± 52	ps
t_L	PLL Lock Time				1	ms
t_R / t_F	Output Rise/Fall Time; NOTE 7	20% to 80%	200		700	ps
odc	Output Duty Cycle		45	50	55	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Measured from the differential input crossing point to the differential output crossing point.

NOTE 2: Defined as the time difference between the input reference clock and the averaged feedback input signal across all conditions, when the PLL is locked and the input reference frequency is stable.

NOTE 3: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential cross points.

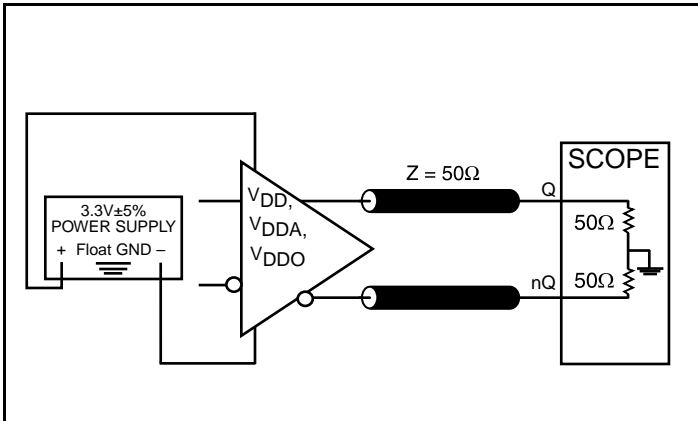
NOTE 4: Phase jitter is dependent on the input source used.

NOTE 5: This parameter is defined in accordance with JEDEC Standard 65.

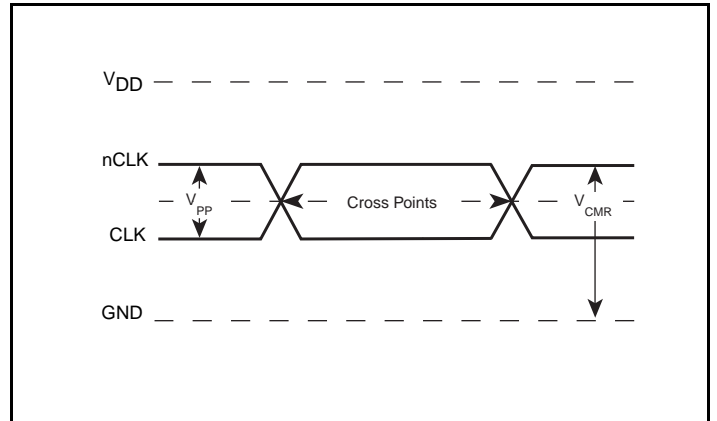
NOTE 6: Characterized at VCO frequency of 622MHz.

NOTE 7: Measured from the 20% to 80% points. Guaranteed by characterization. Not production tested.

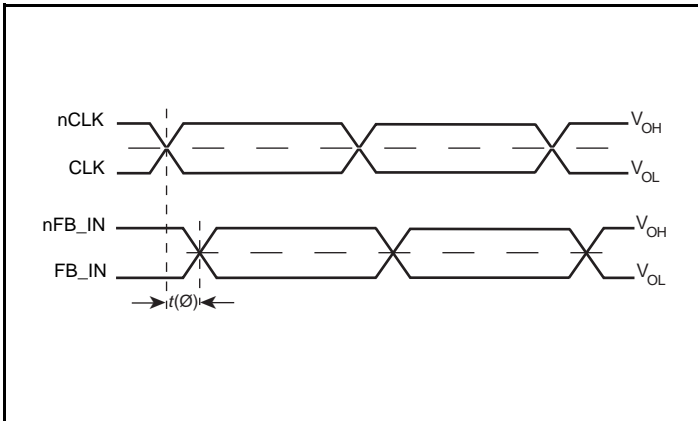
Parameter Measurement Information



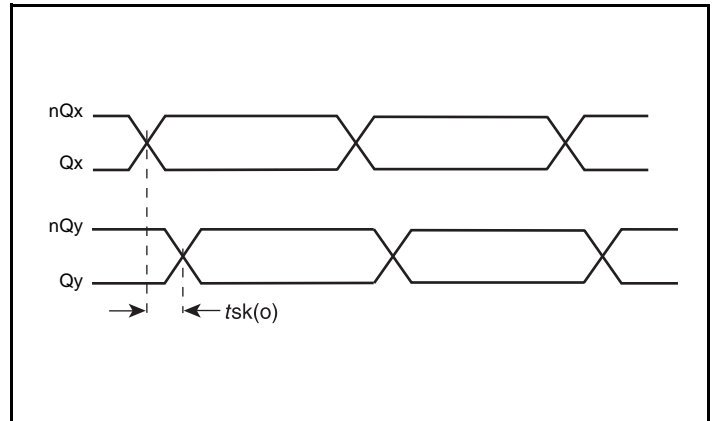
3.3V LVDS Output Load AC Test Circuit



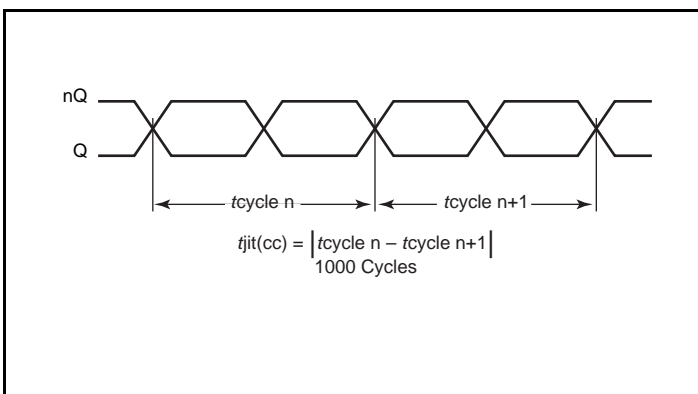
Differential Input Level



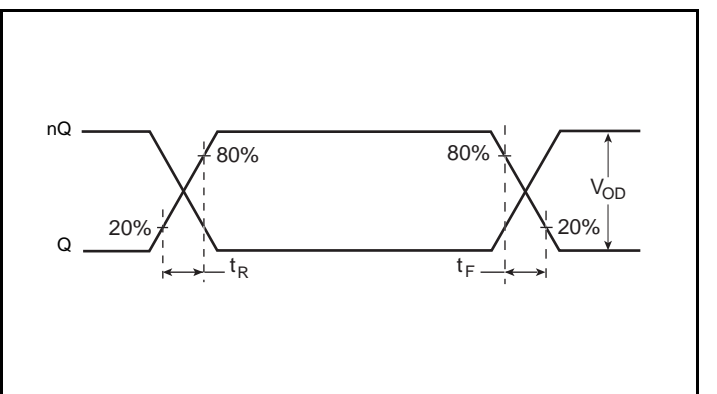
Phase Jitter and Static Phase Offset



Output Skew

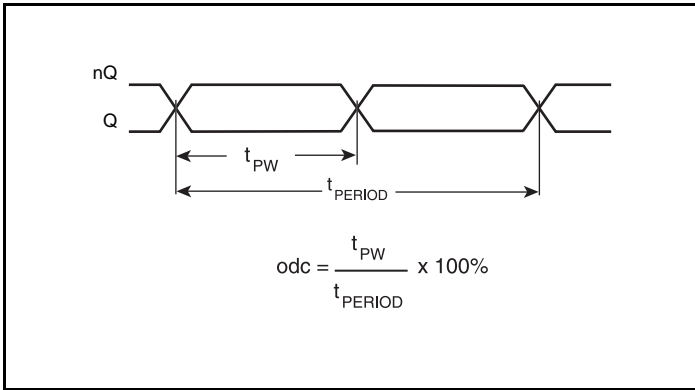


Cycle-to-Cycle Jitter

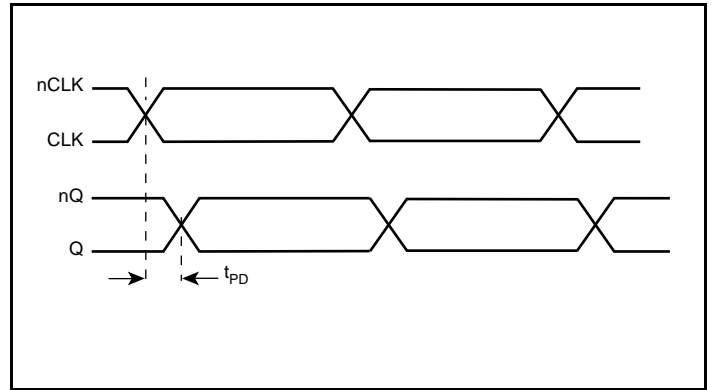


Output Rise/Fall Time

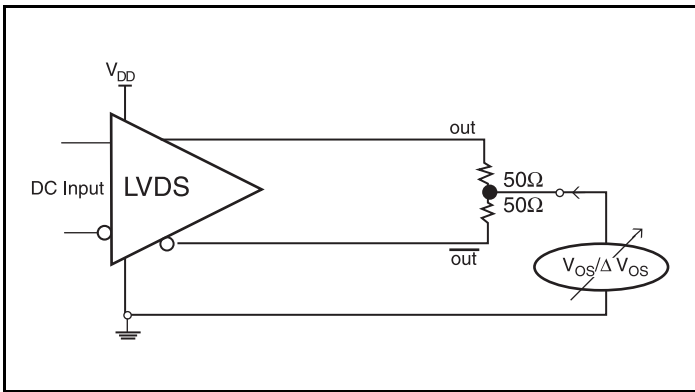
Parameter Measurement Information, continued



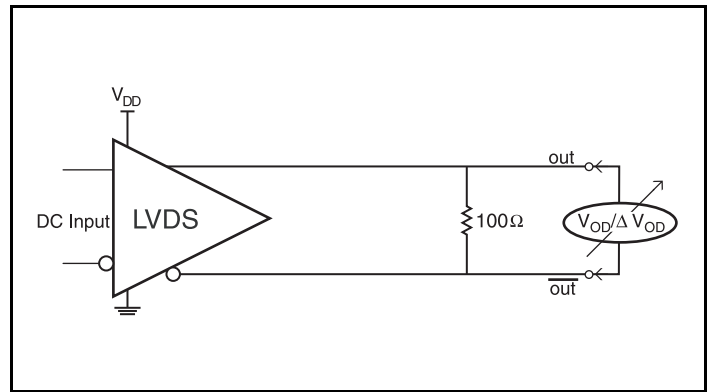
Output Duty Cycle



Propagation Delay



Offset Voltage Setup



Differential Output Voltage Setup

Applications Information

Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 8745BI-21 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. V_{DD} , V_{DDA} and V_{DDO} should be individually connected to the power supply plane through vias, and $0.01\mu\text{F}$ bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic V_{DD} pin and also shows that V_{DDA} requires that an additional 10Ω resistor along with a $10\mu\text{F}$ bypass capacitor be connected to the V_{DDA} pin.

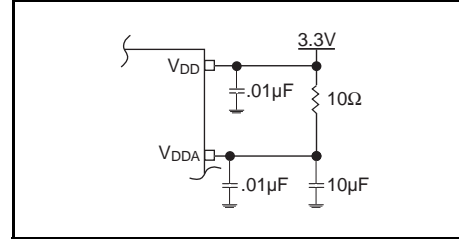


Figure 1. Power Supply Filtering

Wiring the Differential Input to Accept Single-Ended Levels

Figure 2 shows how a differential input can be wired to accept single ended levels. The reference voltage $V_{REF} = V_{DD}/2$ is generated by the bias resistors $R1$ and $R2$. The bypass capacitor ($C1$) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of $R1$ and $R2$ might need to be adjusted to position the V_{REF} in the center of the input voltage swing. For example, if the input clock swing is 2.5V and $V_{DD} = 3.3\text{V}$, $R1$ and $R2$ value should be adjusted to set V_{REF} at 1.25V . The values below are for when both the single ended swing and V_{DD} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (R_o) and the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, $R3$ and $R4$ in parallel should equal the transmission

line impedance. For most 50Ω applications, $R3$ and $R4$ can be 100Ω . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than -0.3V and V_{IH} cannot be more than $V_{DD} + 0.3\text{V}$. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

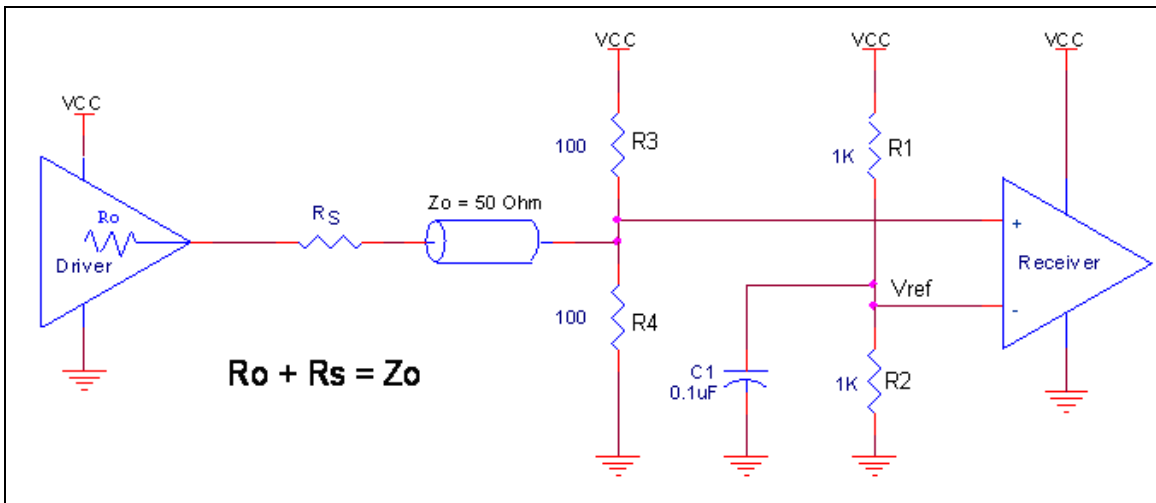
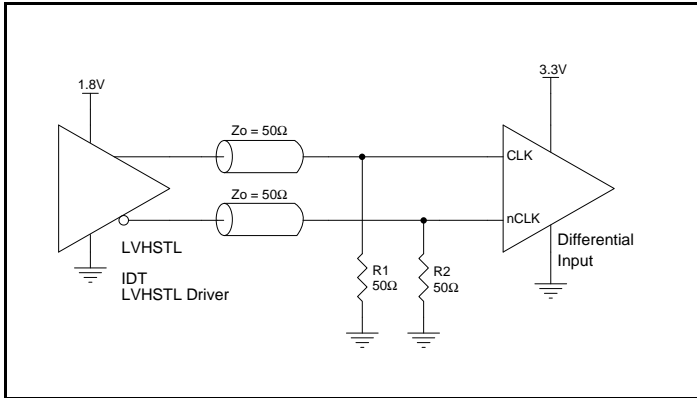


Figure 2. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPECL, LVHSTL, SSTL, HCSL and other differential signals. Both differential signals must meet the V_{PP} and V_{CMR} input requirements. Figures 3A to 3F show interface examples for the CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only.

Please consult with the vendor of the driver component to confirm the driver termination requirements. For example, in Figure 3A, the input termination applies for IDT open emitter LVHSTL drivers. If you are using an LVHSTL driver from another vendor, use their termination recommendation.



3A. CLK/nCLK Input Driven by an IDT Open Emitter LVHSTL Driver

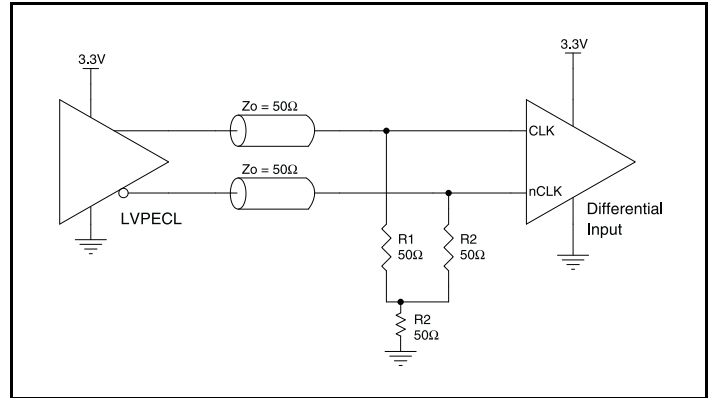


Figure 3B. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

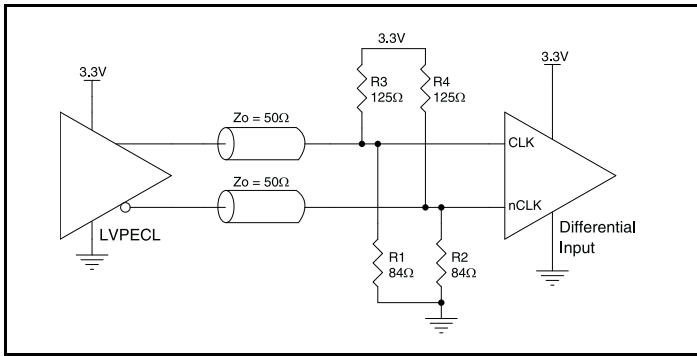


Figure 3C. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

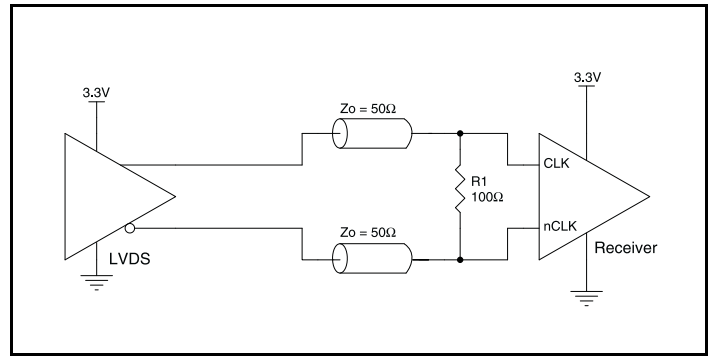


Figure 3D. CLK/nCLK Input Driven by a 3.3V LVDS Driver

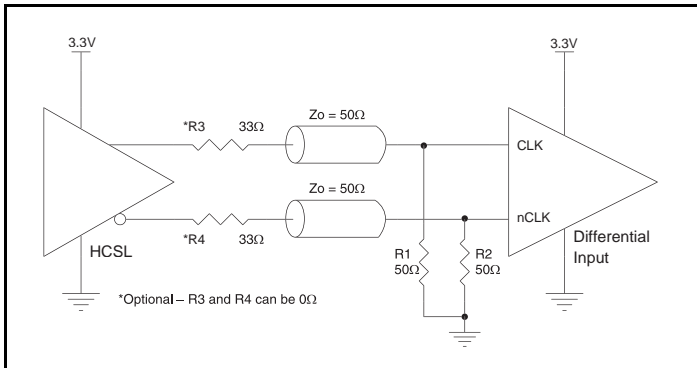


Figure 3E. CLK/nCLK Input Driven by a 3.3V HCSL Driver

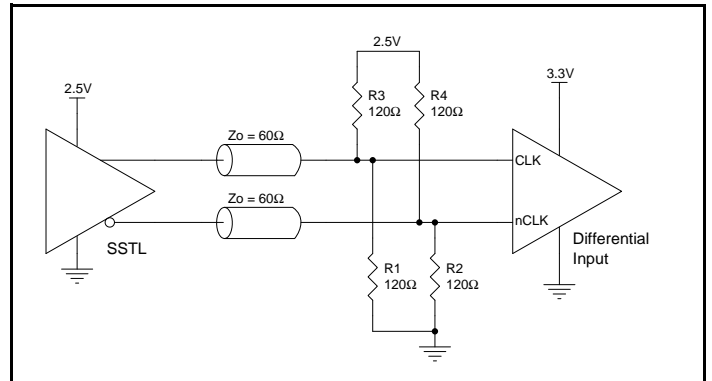


Figure 3F. CLK/nCLK Input Driven by a 2.5V SSTL Driver

Recommendations for Unused Input and Output Pins

Inputs:

LVC MOS Control Pins

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

CLK/nCLK Input

For applications not requiring the use of the differential input, both CLK and nCLK can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from CLK to ground.

Outputs:

LVDS Output

All unused LVDS output pairs can be either left floating or terminated with 100 Ω across. If they are left floating, we recommend that there is no trace attached.

LVDS Driver Termination

A general LVDS interface is shown in *Figure 4*. Standard termination for LVDS type output structure requires both a 100 Ω parallel resistor at the receiver and a 100 Ω differential transmission line environment. In order to avoid any transmission line reflection issues, the 100 Ω resistor must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard

termination schematic as shown in *Figure 4* can be used with either type of output structure. If using a non-standard termination, it is recommended to contact IDT and confirm if the output is a current source or a voltage source type structure. In addition, since these outputs are LVDS compatible, the amplitude and common mode input range of the input receivers should be verified for compatibility with the output.

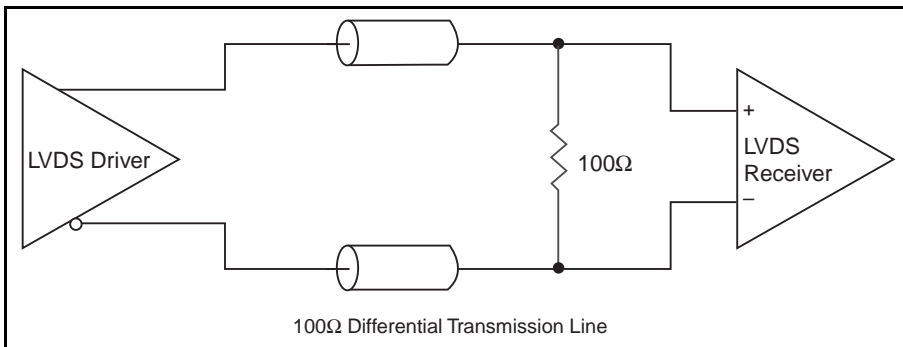


Figure 4. Typical LVDS Driver Termination

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 5*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor’s Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.

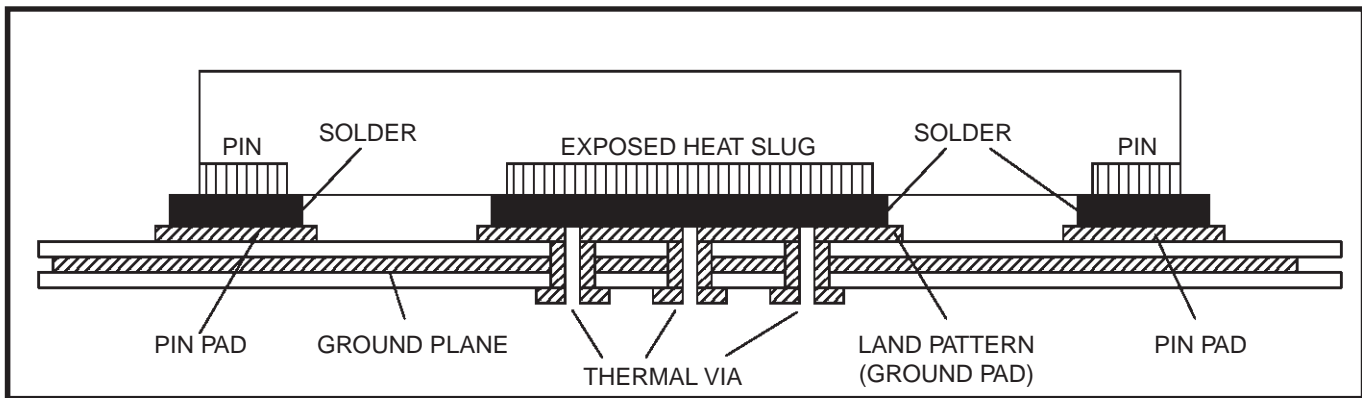


Figure 5. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Schematic Example

The schematic of the 8745BI-21 layout example is shown in *Figure 6A*. The 8745BI-21 recommended PCB board layout for this example is shown in *Figure 6B*. This layout example is used as a general

guideline. The layout in the actual system will depend on the selected component types, the density of the components, the density of the traces, and the stack up of the P.C. board.

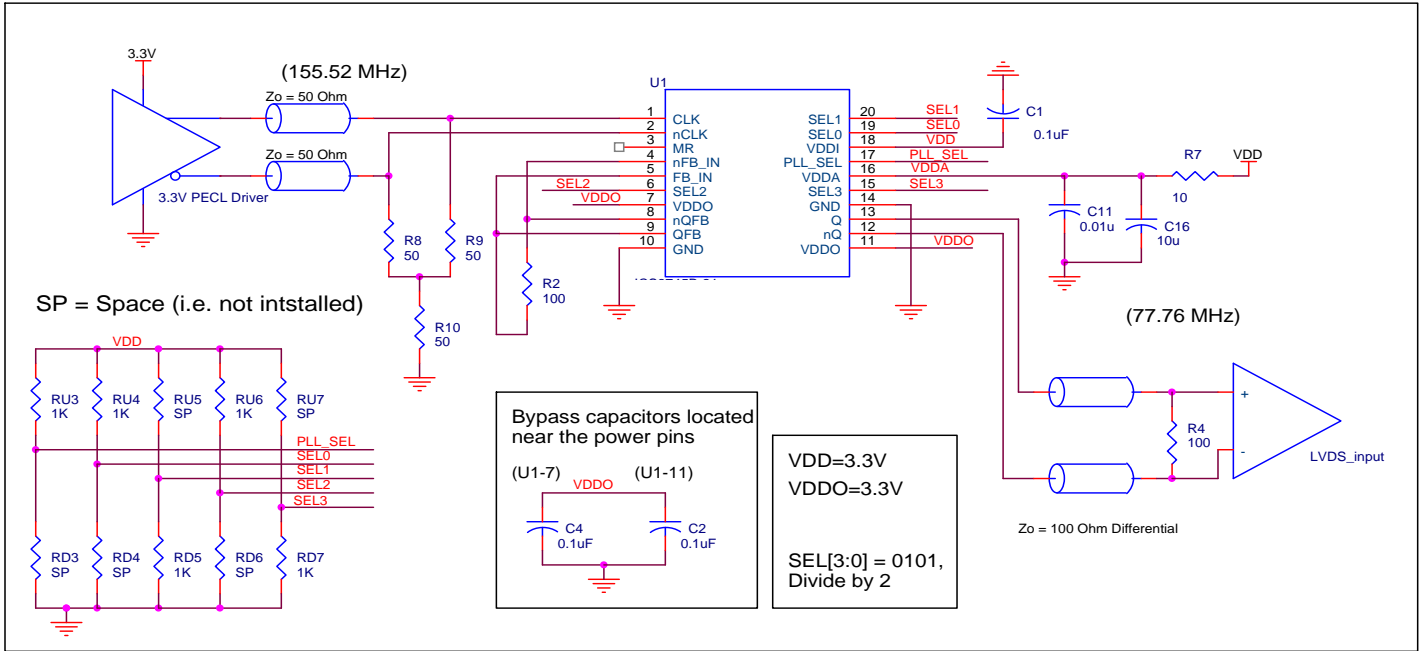


Figure 6A. 8745BI-21 LVDS Zero Delay Buffer Schematic Example

The following component footprints are used in this layout example.

All the resistors and capacitors are size 0603.

Power and Grounding

Place the decoupling capacitors as close as possible to the power pins. If space allows, placement of the decoupling capacitor on the component side is preferred. This can reduce unwanted inductance between the decoupling capacitor and the power pin caused by the via.

Maximize the power and ground pad sizes and number of vias capacitors. This can reduce the inductance between the power and ground planes and the component power and ground pins.

The RC filter consisting of R7, C11, and C16 should be placed as close to the V_{DDA} pin as possible.

Clock Traces and Termination

Poor signal integrity can degrade the system performance or cause system failure. In synchronous high-speed digital systems, the clock signal is less tolerant to poor signal integrity than other signals. Any ringing on the rising or falling edge or excessive ring back can cause system failure. The shape of the trace and the trace delay might be

restricted by the available space on the board and the component location. While routing the traces, the clock signal traces should be routed first and should be locked prior to routing other signal traces.

- The differential 50Ω output traces should have the same length.
- Avoid sharp angles on the clock trace. Sharp angle turns cause the characteristic impedance to change on the transmission lines.
- Keep the clock traces on the same layer. Whenever possible, avoid placing vias on the clock traces. Placement of vias on the traces can affect the trace characteristic impedance and hence degrade signal integrity.
- To prevent cross talk, avoid routing other signal traces in parallel with the clock traces. If running parallel traces is unavoidable, allow a separation of at least three trace widths between the differential clock trace and the other signal trace.
- Make sure no other signal traces are routed between the clock trace pair.
- The matching termination resistors should be located as close to the receiver input pins as possible.

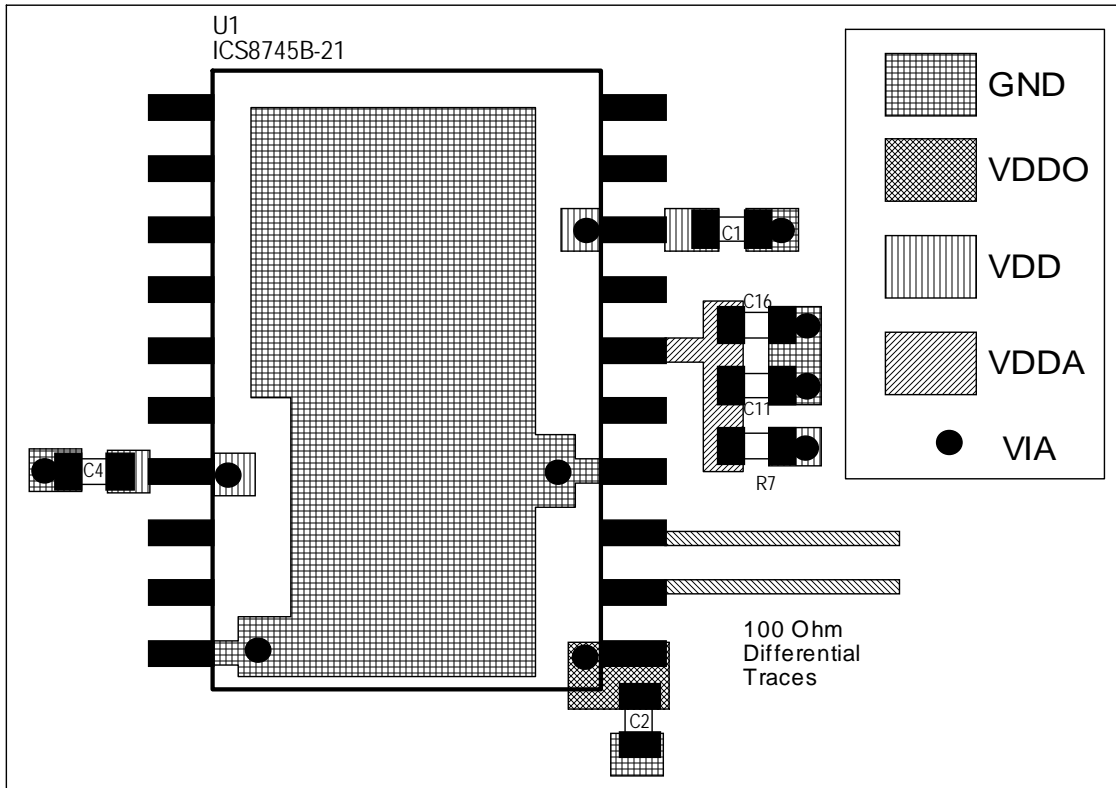


Figure 6B. PCB Board Layout for 8745BI-21

Power Considerations

This section provides information on power dissipation and junction temperature for the 8745BI-21. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 8745BI-21 is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{DD_MAX} * (I_{DD_MAX} + I_{DDA_MAX}) = 3.465V * (128mA + 18mA) = \mathbf{506mW}$
- Power (outputs)_{MAX} = $V_{DDO_MAX} * I_{DDO_MAX} = 3.465V * 62mA = \mathbf{215mW}$

Total Power_{MAX} = 506mW + 215mW = **721mW**

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 46.2°C/W per Table 7A below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.721\text{W} * 46.2^\circ\text{C/W} = 118.3^\circ\text{C}. \text{ This is well below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 7A. Thermal Resistance θ_{JA} for 20 Lead SOIC, Forced Convection

θ_{JA} vs. Air Flow			
Linear Feet per Minute	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	83.2°C/W	65.7°C/W	57.5°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	46.2°C/W	39.7°C/W	36.8°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

Table 7B. Thermal Resistance θ_{JA} for 32 Lead VFQFN, Forced Convection

θ_{JA} vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	37.0°C/W	32.4°C/W	29.0°C/W

PROPOSED

Reliability Information

Table 8A. θ_{JA} vs. Air Flow Table for a 20 Lead SOIC

θ_{JA} vs. Air Flow			
Linear Feet per Minute	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	83.2°C/W	65.7°C/W	57.5°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	46.2°C/W	39.7°C/W	36.8°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

Table 8B. θ_{JA} vs. Air Flow Table for a 32 Lead VFQFN

θ_{JA} vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	37.0°C/W	32.4°C/W	29°C/W

PROPOSED

Transistor Count

The transistor count for 8745BI-21 is: 2772

Package Outline and Package Dimensions

Package Outline - M Suffix for 20 Lead SOIC

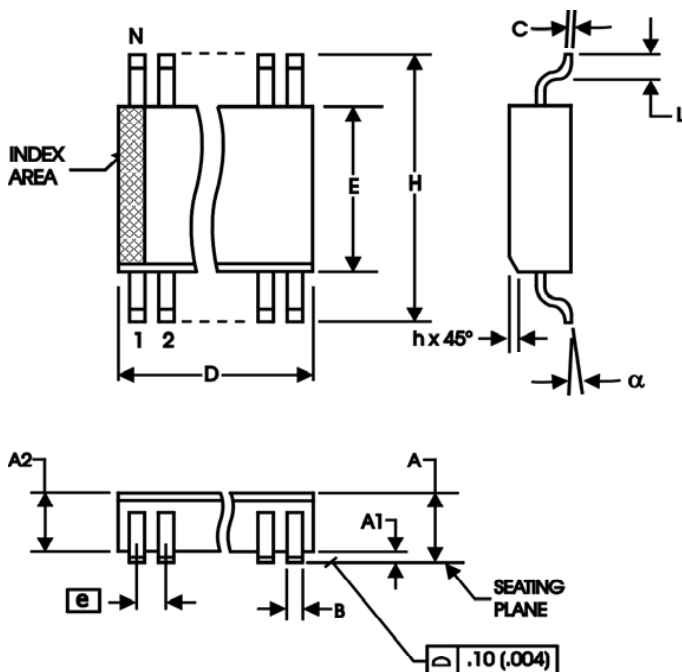


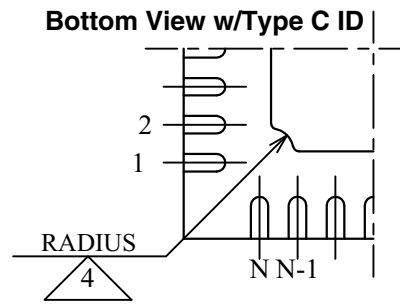
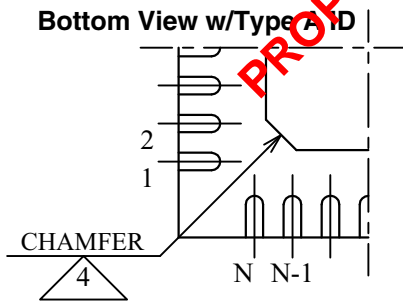
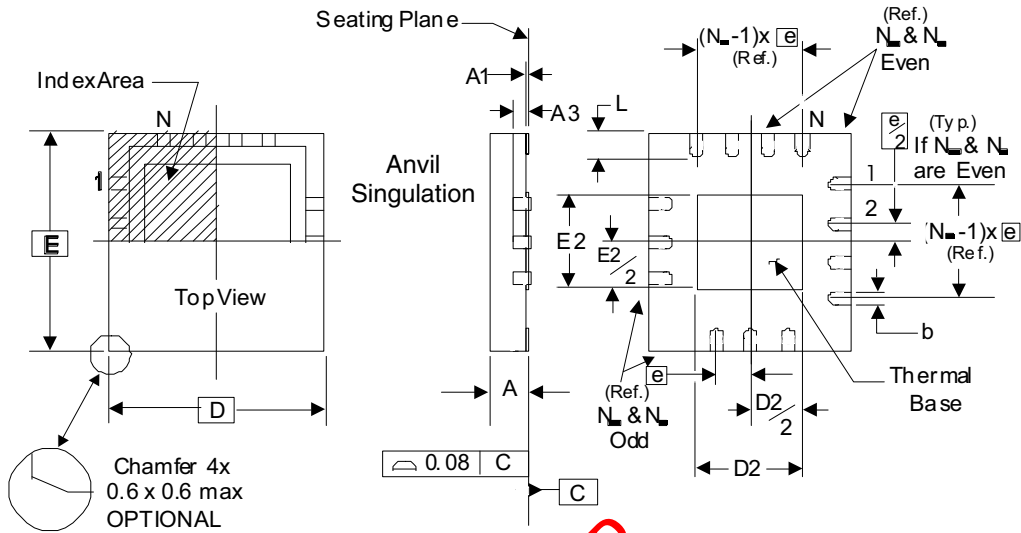
Table 9A. Package Dimensions for 20 Lead SOIC

300 Millimeters All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	20	
A		2.65
A1	0.10	
A2	2.05	2.55
B	0.33	0.51
C	0.18	0.32
D	12.60	13.00
E	7.40	7.60
e	1.27 Basic	
H	10.00	10.65
h	0.25	0.75
L	0.40	1.27
α	0°	7°

Reference Document: JEDEC Publication 95, MS-013, MS-119

Package Outline and Package Dimensions

Package Outline - K Suffix for 32 Lead VFQFN



There are 2 methods of indicating pin 1 corner at the back of the VFQFN package:

1. Type A: Chamfer on the paddle (near pin 1)
2. Type C: Mouse bite on the paddle (near pin 1)

Table 9B. Package Dimensions

JEDEC Variation: VHHD-2/-4			
All Dimensions in Millimeters			
Symbol	Minimum	Nominal	Maximum
N	32		
A	0.80		1.00
A1	0		0.05
A3	0.25 Ref.		
b	0.18	0.25	0.30
N_D & N_E	8		
D & E	5.00 Basic		
D2 & E2	3.0		3.3
e	0.50 Basic		
L	0.30	0.40	0.50

NOTE: The following package mechanical drawing is a generic drawing that applies to any pin count VFQFN package. This drawing is not intended to convey the actual pin count or pin layout of this device. The pin count and pinout are shown on the front page. The package dimensions are in Table 9B.

Reference Document: JEDEC Publication 95, MO-220

Ordering Information

Table 10. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
8745BMI-21	ICS8745BMI-21	20 Lead SOIC	Tube	-40°C to 85°C
8745BMI-21T	ICS8745BMI-21	20 Lead SOIC	Tape & Reel	-40°C to 85°C
8745BMI-21LF	ICS8745BMI-21LF	"Lead-Free" 20 Lead SOIC	Tube	-40°C to 85°C
8745BMI-21LFT	ICS8745BMI-21LF	"Lead-Free" 20 Lead SOIC	Tape & Reel	-40°C to 85°C
8745BKI-21LF	ICS745BI21L	"Lead-Free" 32 Lead VFQFN	Tray	-40°C to 85°C
8745BKI-21LFT	ICS745BI21L	"Lead-Free" 32 Lead VFQFN	Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

Revision History Sheet

Rev	Table	Page	Description of Change	Date
B	T4D	5	LVDS DC Characteristics Table - modified VOS 0.90V min. to 1.05V min, 1.15V typical to 1.2V typical, and 1.4V max. to 1.35V max.	3/17/04
C	T6	7 12 15	AC Characteristics Table - changed t_{PD} max limit from 3.9ns to 4.0ns. Added Recommendations for Unused Input & Output Pins. Added Power Considerations section. Updated format throughout the datasheet.	4/17/07
C	T3A T 3B T4C T6 T10	1 3 4 6 7 10 11 17	Pin Assignment - corrected lineup of pin names. Control Input Function Table - deleted "z" from 1st row of SEL3 column. PLL Bypass Function Table - deleted "z" from 1st row of SEL3 column Differential DC Characteristics Table - updated NOTES. AC Characteristics Table - added thermal note. Power Supply Filtering Technique - updated paragraph. Updated <i>Differential Clock Input Interface</i> . Ordering Information Table - added "LF" marking. Deleted "ICS" prefix in Part/Order number column. Updated Header/Footer of datasheet.	1/25/10
D	T7B T8B T9B T10	1 5 10 12 13 16 17 18 19	Added 32 Lead VFQFN proposed pin assignment. Absolute Maximum Ratings - added 32 Lead VFQFN Package Thermal Impedance. Updated <i>Wiring the Differential Input to Accept Single-ended Levels</i> . Updated <i>LVDS Output Termination</i> . Added <i>VFQFN EPad Thermal Release section</i> . Added proposed <i>32 Lead VFQFN Thermal Resistance table</i> . Added proposed <i>32 Lead VFQFN theta ja table</i> . Added proposed <i>32 Lead VFQFN Package Outline and Dimensions</i> . Ordering Information Table added proposed <i>32 Lead VFQFN ordering information</i> .	7/28/10
D		1	Product Discontinuation Notice - Last time buy expires November 2, 2016. PDN# CQ-15-05.	11/6/15
E			Per PDN# CQ-15-05 obsolete datasheet.	1/10/17

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